

# Si Zener-diode Chip—TK0V09ZDN

## 1. Scope

- The specification applies to planar Zener diode.
- Extra lower leakage current ,high voltage pressure defense.
- Special assembly process in high-power LED

## 2. Structure

- Planar type Zener diode.
- Electrode P (anode) : Aluminum. (Gold for option)
- Electrode N (cathode) side : Gold.

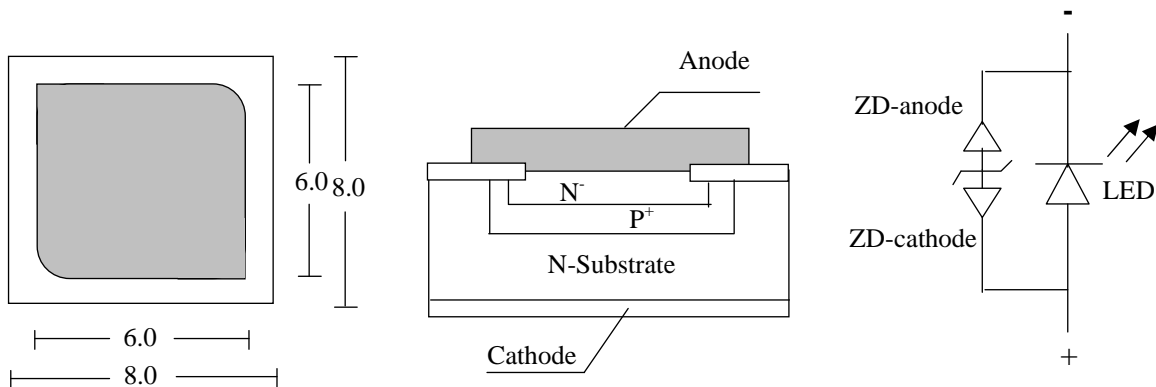
## 3. Size

- Chip size : 8.0mil × 8.0mil ± 0.8mil (0.2032mm × 0.2032mm ± 0.020mm)
- Thickness : 4.0mil / 6.0mil ± 0.6mil (0.110mm / 0.152mm ± 0.015mm)
- Pad Size : 6.0mil × 6.0mil ± 0.4mil (0.152mm × 0.152mm ± 0.010mm)
- Pattern drawing : per fig. 1

## 4. Electrical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	$V_F$	$I_F = 10\text{mA}$	6		8	V
Forward Leakage current	$I_F$	$V_F = 5\text{V}$			500	nA
Reverse Voltage	$V_Z$	$I_R = 10\text{mA}$	30			V
Reverse Leakage current	$I_R$	$V_R = 5\text{V}$			500	nA



Unit : mil

fig. 1

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